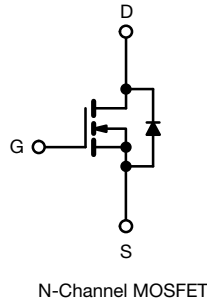
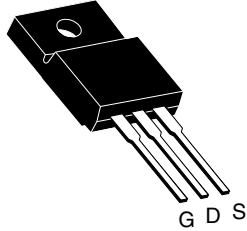


## E Series Power MOSFET

**TO-220 FULLPAK**


### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	700	
$R_{DS(on)}$ max. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.6
$Q_g$ max. (nC)	48	
$Q_{gs}$ (nC)	6	
$Q_{gd}$ (nC)	11	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free and Halogen-free	SiHF6N65E-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	650	V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>e</sup>	$V_{GS}$ at 10 V	$T_C = 25$ °C	7	A
		$T_C = 100$ °C	5	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	18		
Linear Derating Factor		0.63	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	56	mJ	
Maximum Power Dissipation	$P_D$	31	W	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C	
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125$ °C	37	V/ns
Reverse Diode $dV/dt$ <sup>d</sup>		27		
Soldering Recommendations (Peak temperature) <sup>c</sup>	For 10 s	300	°C	
Mounting Torque	M3 screw	0.6	Nm	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 2$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.
- Limited by maximum junction temperature.



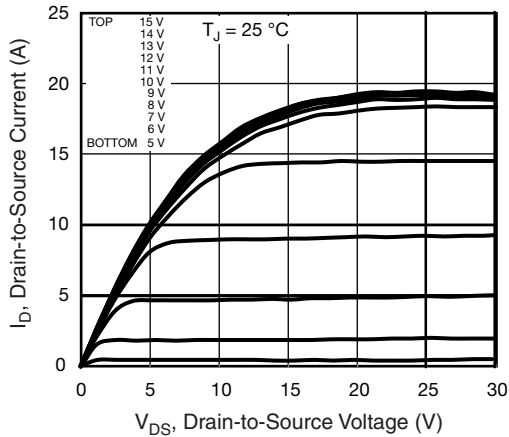
<b>THERMAL RESISTANCE RATINGS</b>				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R <sub>thJA</sub>	-	65	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	4.0	

<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		650	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.73	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2	-	4	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
		V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	10	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3 A	-	0.5	0.6	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 3 A		-	2	-	S
<b>Dynamic</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz		-	820	-	pF
Output Capacitance	C <sub>oss</sub>			-	40	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	4	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	C <sub>o(er)</sub>			-	36	-	
Effective Output Capacitance, Time Related <sup>b</sup>	C <sub>o(tr)</sub>	V <sub>DS</sub> = 0 V to 520 V, V <sub>GS</sub> = 0 V		-	117	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3 A, V <sub>DS</sub> = 520 V	-	24	48	nC
Gate-Source Charge	Q <sub>gs</sub>			-	6	-	
Gate-Drain Charge	Q <sub>gd</sub>			-	11	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 520 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	14	28	ns
Rise Time	t <sub>r</sub>			-	12	24	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	30	60	
Fall Time	t <sub>f</sub>			-	20	40	
Gate Input Resistance	R <sub>g</sub>			f = 1 MHz, open drain		-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	18	
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V		-	-	1.3	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 3 A, di/dt = 100 A/μs, V <sub>R</sub> = 25 V		-	237	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>			-	2.2	-	μC
Reverse Recovery Current	I <sub>RRM</sub>			-	16	-	A

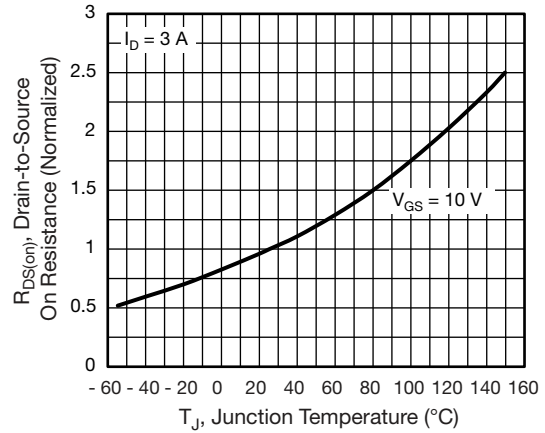
**Notes**

- a. C<sub>oss(er)</sub> is a fixed capacitance that gives the same energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 % to 80 % V<sub>DSS</sub>.
- b. C<sub>oss(tr)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 % to 80 % V<sub>DSS</sub>.

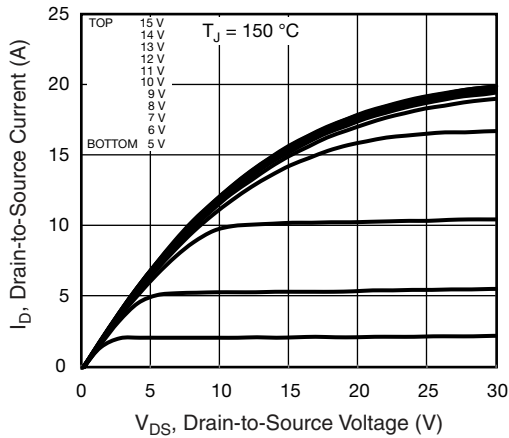
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



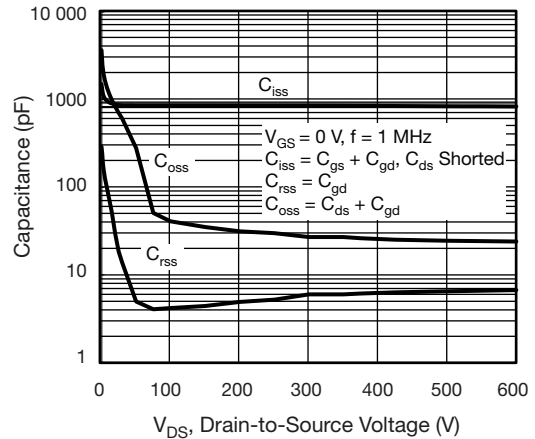
**Fig. 1 - Typical Output Characteristics**



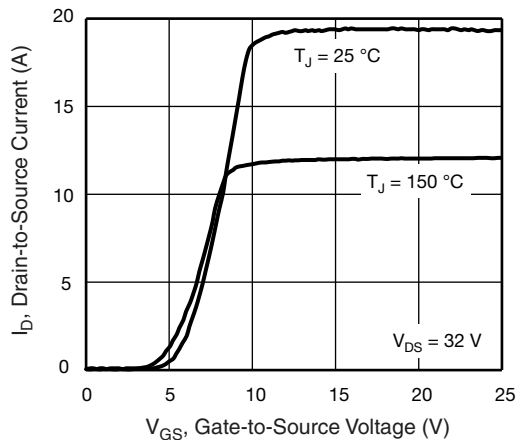
**Fig. 4 - Normalized On-Resistance vs. Temperature**



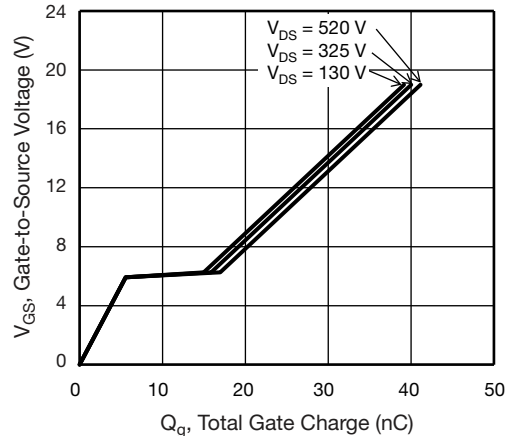
**Fig. 2 - Typical Output Characteristics**



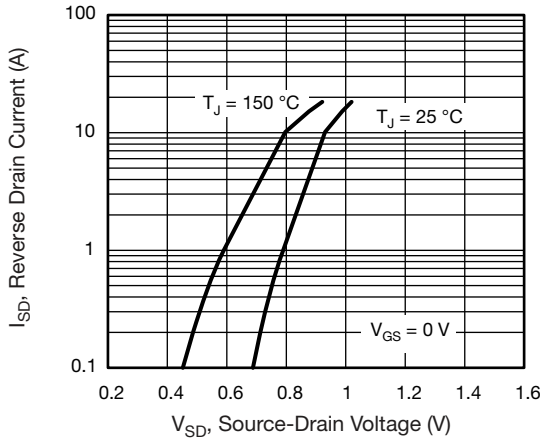
**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



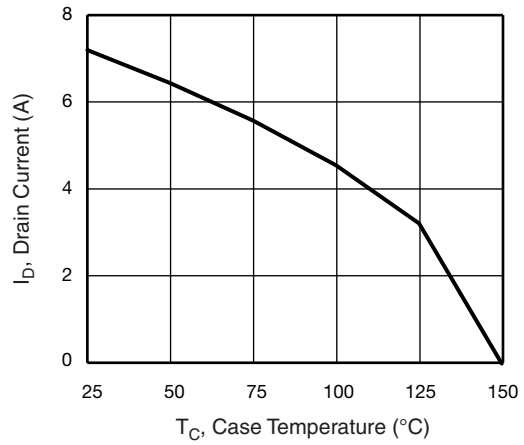
**Fig. 3 - Typical Transfer Characteristics**



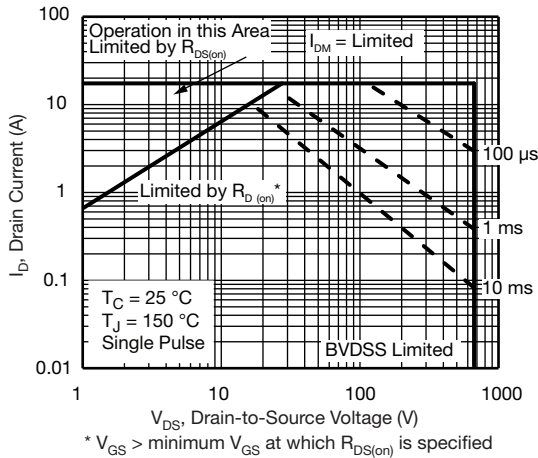
**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



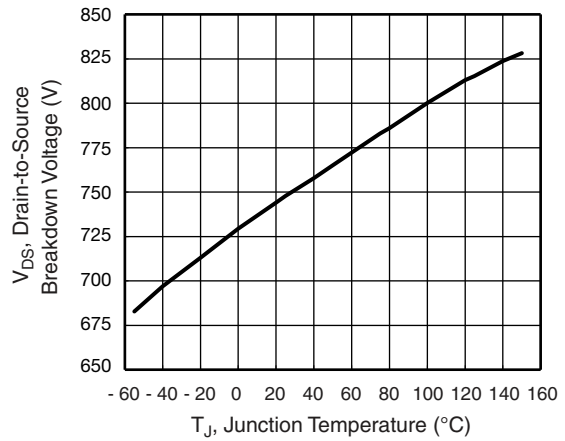
**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



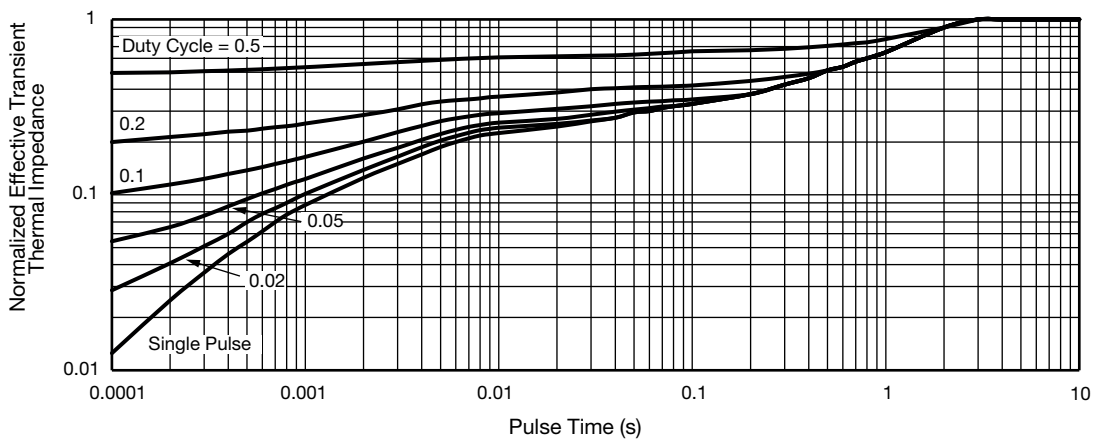
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 8 - Maximum Safe Operating Area**



**Fig. 10 - Temperature vs. Drain-to-Source Voltage**



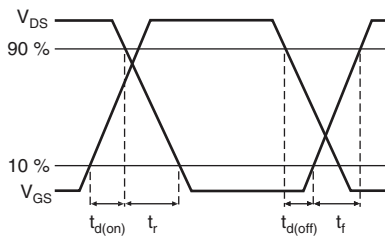
**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**



**Fig. 12 - Switching Time Test Circuit**



**Fig. 16 - Basic Gate Charge Waveform**



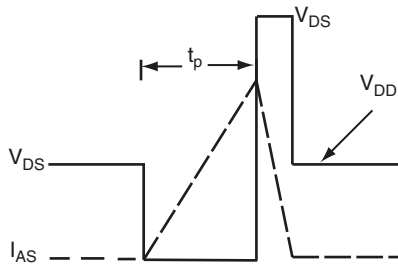
**Fig. 13 - Switching Time Waveforms**



**Fig. 17 - Gate Charge Test Circuit**

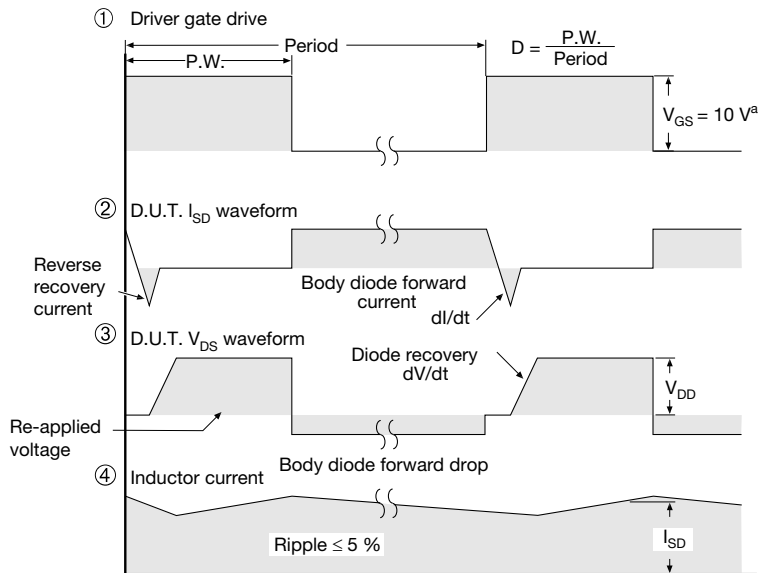
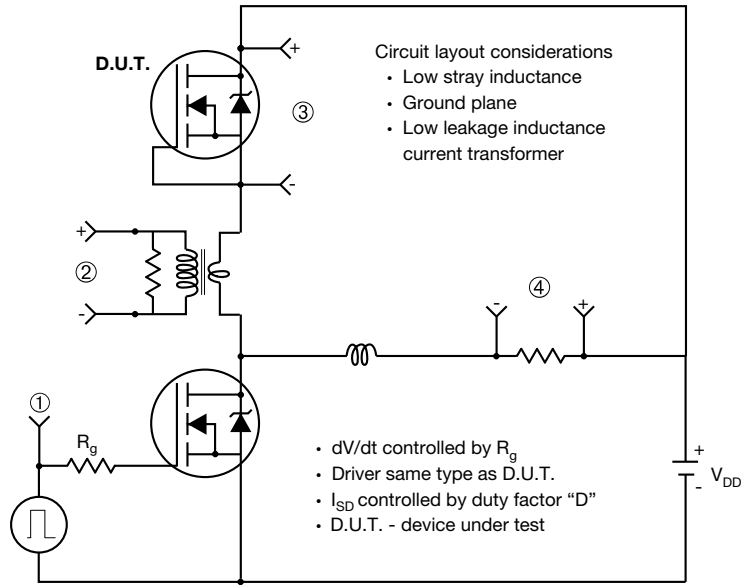


**Fig. 14 - Unclamped Inductive Test Circuit**



**Fig. 15 - Unclamped Inductive Waveforms**

**Peak Diode Recovery dV/dt Test Circuit**



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

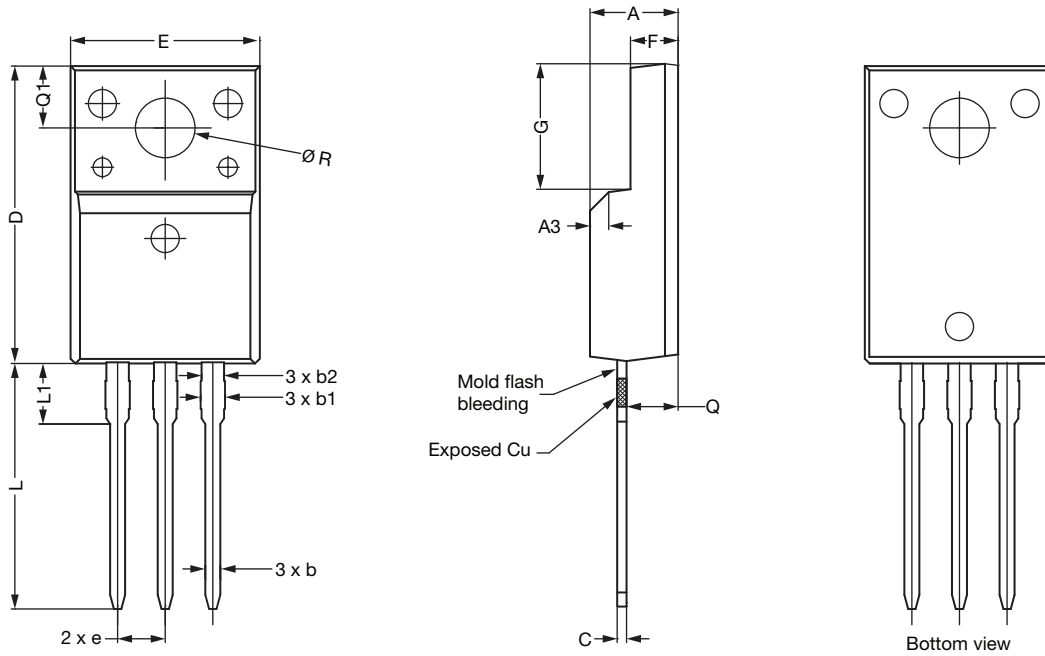
**Fig. 18 - For N-Channel**

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# TO-220 FULLPAK (High Voltage)

## OPTION 1: FACILITY CODE = 9



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
$\varnothing R$	3.08	3.18	3.28

### Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking



OPTION 2: FACILITY CODE = Y



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019  
DWG: 5972

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking





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